TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

# 2SC2782

#### VHF BAND POWER AMPLIFIER APPLICATIONS

Output Power

: Po = 80W (Min.)

 $(f = 175MHz, V_{CC} = 12.5V, Pi = 18W)$ 

#### MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	36	V
Collector-Emitter Voltage	V <sub>CEO</sub>	16	V
Emitter-Base Voltage	V <sub>EBO</sub>	4	V
Collector Current	Ι <sub>C</sub>	20	А
Collector Power Dissipation	PC	220	W
Junction Temperature	Tj	175	°C
Storage Temperature Range	T <sub>stg</sub>	-65~175	°C



Weight: 5.5g

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## ELECTRICAL CHARACTERISTICS (Tc = 25°C)

CHARACTERISTIC	CHARACTERISTIC SYMBOL TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	V (BR) CBO	I <sub>C</sub> = 20mA, I <sub>E</sub> = 0	36	_	_	V
Collector-Emitter Breakdown Voltage	V (BR) CEO	I <sub>C</sub> = 50mA, I <sub>B</sub> = 0	16	_	_	V
Emitter-Base Breakdown Voltage	V (BR) EBO	I <sub>E</sub> = 1mA, I <sub>C</sub> = 0	4	_	_	V
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10A *	10	_	_	
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 12.5V, I <sub>E</sub> = 0 f = 1MHz	_	_	320	pF
Output Power	Po	(Fig.) V <sub>CC</sub> = 12.5V, f = 175MHz	80	90		W
Power Gain	Gp		6.4	6.8	_	dB
Collector Efficiency	η <sub>C</sub>	Pi = 18W	60	70	_	%
Series Equivalent Input Impedance	Z <sub>in</sub>	V <sub>CC</sub> = 12.5V	_	1.0 +j1.5	_	Ω
Series Equivalent Output Impedance	Z <sub>out</sub>	f = 175MHz, Po = 80W	_	1.2 +j1.8	_	Ω

\* Pulse Test: Pulse Width  $\leq$  100µs, Duty Cycle  $\leq$  3%

#### CAUTION

Beryllia Ceramics is used in this product. The dust or vapor can be dangerous to humans. Do not break, cut, crush or dissolve chemically. Dispose of this product properly according to law. Do not intermingle with normal industrial or domestic waste.

# **TOSHIBA**

### Fig. Po TEST CIRCUIT



$C_1 \sim C_4$	: $\sim 20 \mathrm{pF}$
$C_5$	: 156pF (39pF $\times$ 4) CERAMIC CONDENSER
$C_6$	: $132 pF (33 pF \times 4)$ CERAMIC CONDENSER
$C_7$	: $0.01 \mu$ F CERAMIC CONDENSER
C <sub>8</sub>	: $10 \mu F$
$L_1, L_3$	: $\phi 1.5$ mm SILVER PLATED COPPER WIRE, 10ID, 1T
$L_2$	: $\phi 1.5$ mm SILVER PLATED COPPER WIRE, 10ID, 2T
RFC	: $\phi$ 1mm ENAMEL COATED COPPER WIRE, 6ID, 10T
$\mathbf{FB}$	: FERRITE BEAD



#### CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.